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[14a-B1-1] 13.8 Compound and power electron devices and process technology

Seiji Nakamura (TMU)

Wed. Sep 14, 2016 11:45 AM - 12:15 PM  B1 (Exhibition Hall)

△: Presentation by Applicant for JSAP Young Scientists Presentation Award
▲: English Presentation
▼: Both of Above
No Mark: None of Above

11:45 AM - 12:15 PM

[14a-B1-1] [JSAP Paper Award Speech] Characterization of electronic states at insulator/(Al)GaN interfaces for improved insulated gate and surface passivation structures of GaN-based transistors

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